



## TECHNICAL DATASHEET

The *AMP600900-50W-28V* is a 50W high gain Solid State High Power Amplifier.

This amplifier module utilizes the latest high power RF GaN transistors.

This amplifier is suitable for jamming .

### Features

600-900MHz frequency range

Psat 47dBm Min

Power gain 45dB

50 ohm input/output impedance

Solid-state Class AB Broadband design

Instantaneous ultra-broadband

Small and light weight

High reliability and ruggedness

### ELECTRICAL SPECIFICATIONS(T=50°C,DC Voltage= 28V, 50 System)

PARAMETER	UNIT	MIN	TYP	MAX	SYMBOL
Operating Frequency	MHz	600	-	900	F <sub>o</sub>
Operating Bandwidth	MHz	-	300	-	BW
Peak Output Power @CW Signal	W	-	50	-	PsAT
Input Power	dBm	-	-	-	P <sub>IN</sub>
Maximum Input Power @Without Damage	dBm	-	-	-	P <sub>IN, MAX</sub>
Power Gain @Input Power 0dBm	dB	-	47±2	-	G <sub>p</sub>
Gain Flatness @Input Power 0dBm	dB	-	-	±1	G <sub>p</sub>
Efficiency	%	50	54	55	E <sub>FF</sub>
Harmonics 1 to N @Output Power 50W	dBc	12	13	15	H <sub>N</sub>
Spurious Level	dBc	60	-	-	Spur
Input VSWR	dB	-	-	-	VSWR
Output VSWR	dB	-	-	2:1	VSWR
Operating Voltage	V	24	28	32	V <sub>DC</sub>
Current Consumption @Output Power 50W	A	-	3.3	-	I <sub>DC</sub>



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### MECHANICAL SPECIFICATIONS

PARAMETER	UNIT	TYP
Mass	kg	0.35
Dimension	mm	133.6*46.1*22.0 (With connectors)
RF Connector	-	MCX Female : RF Input
		N Female : RF Output
DC Connector	-	Power Line, Male : Supply
Cooling		External Heat-sink Required

### ENVIRONMENTAL SPECIFICATIONS

PARAMETER	UNIT	RATING	SYMBOL
Operating Case Temperature	°C	-20 ~ 85	T <sub>c</sub>
Storage Temperature	°C	-40 ~ 105	T <sub>STG</sub>
Relative Humidity(Non-condensing)	RH	95	%

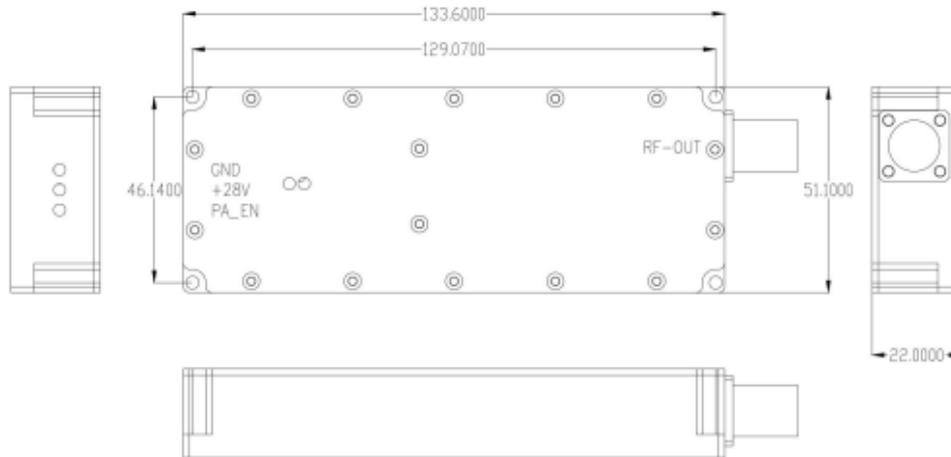
### DC INTERFACE CONNECTOR – [Hybrid D-Sub 9-Pin, Male]

Pin #	Description	Specifications
1	GND	Ground
2	VDD	+28VDC
3	Enable	28V



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### OUTLINE DRAWING [mm]



### Side View [3D]

